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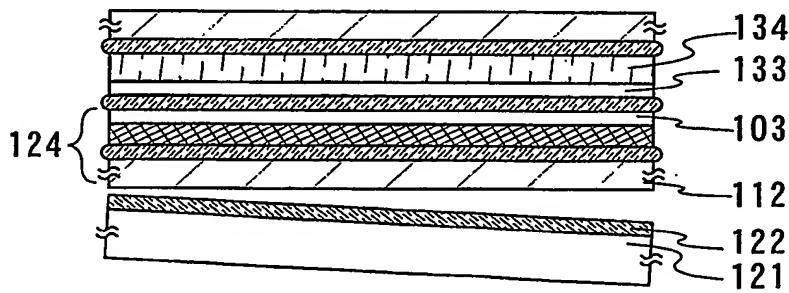
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(54) Title: METHOD OF MANUFACTURING DISPLAY DEVICE



substrate; forming a layer including a pixel on a surface of a third substrate; attaching the layer including the pixel to a fourth substrate; and attaching layers including the optical filter to another surface of the third substrate.

(57) Abstract: To provide a method of manufacturing a display device having an excellent impact resistance property with high yield, in particular, a method of manufacturing a display device having an optical film that is formed using a plastic substrate. The method of manufacturing a display device includes the steps of: sequentially forming a metal film, an oxide film, and an optical filter on a first substrate; separating layers including the optical filter from the first substrate; attaching layers including the optical filter to a second